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The invention relates to the electronics, in particular to the semiconductor technology.

The process for polysulphide films obtaining includes deposition of the sulphidic compounds onto a support and subsequent thermal treatment. Novelty consists in that the support is preliminarily treated with $ZnCl_2$ solution, dried at the temperature of 373 K, the sulphidic compound $Zn_xIn_2S_{3+x}$ ($x=1, 2, 3, 5$) is mixed with $ZnCl_2$ solution, and the thermal treatment is carried out under the condition $T \cdot t = (6, 3-8, 5) 10^3$ grade·h, where:

T – the treatment temperature,

t – the treatment time.

Claims: 1